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Substitute for form 1449APTO INFORMATION DISCLOSURE	Complete if Known	required to respond to a collection of information unless it contains a valid OMB control number
	Application Number	09/484303
STATEMENT BY APPLICANT (Use as many sheets)	Filing Date	January 18, 2000
0 30	First Named Inventor	Ahn, Kie
) 101 0 3 2003 E	Group Art Unit	2823
Sheet 1 of 3 Ce road Labor	Examiner Name	Berezny, Neal
	Attorney Docket No: 3	03.648US1

	1100.0		ATENT DOCUMENT			
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Group Art Unit	2823
Examiner Name	Berezny, Neal

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Application Number	09/484303
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Sheet 3 of 3	Attorney Docket No: 3	03.648US1

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